



STD2NK100Z STP2NK100Z - STU2NK100Z

N-channel 1000 V, 6.25 Ω , 1.85 A, TO-220, DPAK, IPAK
Zener-protected SuperMESH™ Power MOSFET

Features

| Type | V _{DSS} | R _{DS(on)} max | I _D | P _{TOT} |
|------------|------------------|----------------------------|----------------|------------------|
| STD2NK100Z | 1000 V | < 8.5 Ω | 1.85 A | 70 W |
| STP2NK100Z | 1000 V | < 8.5 Ω | 1.85 A | 70 W |
| STU2NK100Z | 1000 V | < 8.5 Ω | 1.85 A | 70 W |

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Application

- Switching applications

Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, specialties is taken to ensure a very good dv/dt capability for the most demanding application. Such series complements ST full range of high voltage Power MOSFETs.

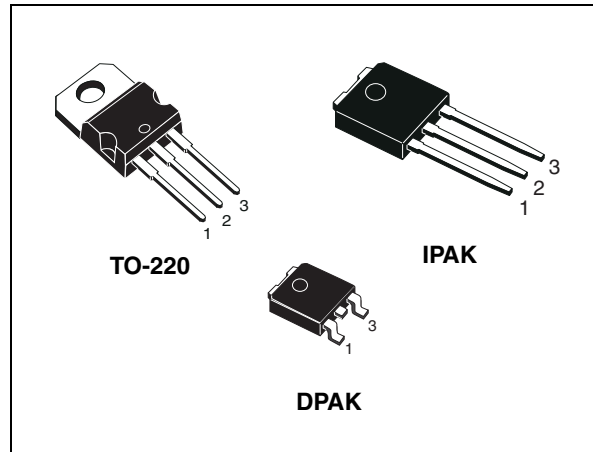


Figure 1. Internal schematic diagram

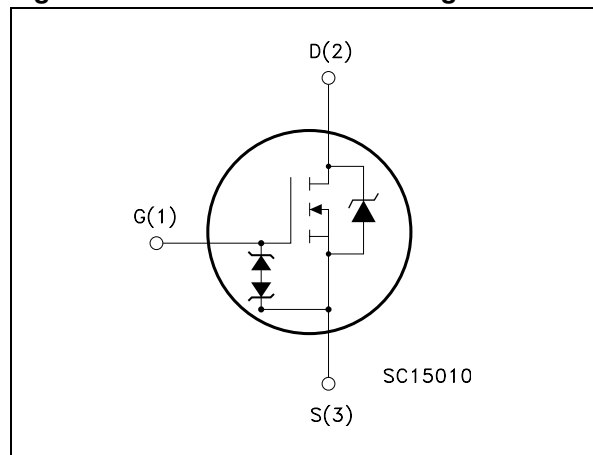


Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|---------|---------|---------------|
| STD2NK100Z | 2NK100Z | DPAK | Tape and reel |
| STP2NK100Z | 2NK100Z | TO-220 | Tube |
| STU2NK100Z | 2NK100Z | IPAK | Tube |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|--------------------|---|------------|---------------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 1000 | V |
| V_{GS} | Gate-source voltage | ± 30 | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 1.85 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 1.16 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 7.4 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 70 | W |
| | Derating factor | 0.56 | W/ $^\circ\text{C}$ |
| $V_{ESD(G-S)}$ | G-S ESD (HBM C=100 pF, R=1.5 k Ω) | 3000 | V |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 2.5 | V/ns |
| T_j T_{stg} | Operating junction temperature Storage temperature | -55 to 150 | $^\circ\text{C}$ |

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 1.85\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

| Symbol | Parameter | Value | | | Unit |
|----------------|---|--------|------|------|---------------------------|
| | | TO-220 | IPAK | DPAK | |
| $R_{thj-case}$ | Thermal resistance junction-case max | 1.79 | | | $^\circ\text{C}/\text{W}$ |
| $R_{thj-pcb}$ | Thermal resistance junction-pcb minimum footprint | -- | -- | 50 | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-amb max | 62.5 | 100 | | $^\circ\text{C}/\text{W}$ |
| T_l | Maximum lead temperature for soldering purpose | 300 | | | $^\circ\text{C}$ |

Table 4. Avalanche data

| Symbol | Parameter | Value | Unit |
|----------------|---|-------|------|
| $I_{AR}^{(1)}$ | Avalanche current, repetitive or not-repetitive | 1.85 | A |
| $E_{AS}^{(2)}$ | Single pulse avalanche energy | 170 | mJ |

1. Pulse width limited by T_{jmax}
2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|---|------|------|----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1 \text{ mA}, V_{GS} = 0$ | 1000 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$ | | | 1 50 | μA μA |
| I_{GSS} | Gate body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 30 \text{ V}$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 50 \mu A$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10 \text{ V}, I_D = 0.9 \text{ A}$ | | 6.25 | 8.5 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|---|--|------|----------------|------|----------------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15 \text{ V}, I_D = 0.9 \text{ A}$ | | 2.4 | | S |
| C_{iss} C_{oss} C_{rss} | Input capacitance Output capacitance Reverse transfer capacitance | $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$ | | 499 53 9 | | pF pF pF |
| $C_{oss \text{ eq.}}^{(2)}$ | Equivalent output capacitance | $V_{GS} = 0, V_{DS} = 0 \text{ to } 800 \text{ V}$ | | 28 | | pF |
| R_G | Gate input resistance | $f = 1 \text{ MHz}, \text{ open drain}$ | | 6.6 | | Ω |
| Q_g Q_{gs} Q_{gd} | Total gate charge Gate-source charge Gate-drain charge | $V_{DD} = 800 \text{ V}, I_D = 1.85 \text{ A}$ $V_{GS} = 10 \text{ V}$ (see Figure 17) | | 16 3 9 | | nC nC nC |

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss \text{ eq.}}$ is defined as constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|----------------------------------|--|------|--------------|------|----------|
| $t_{d(on)}$ t_r | Turn-on delay time Rise time | $V_{DD}= 500\text{ V}$, $I_D= 0.9\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ <i>(see Figure 16)</i> | | 7.2 6.5 | | ns ns |
| $t_{d(off)}$ t_r | Turn-off delay time Fall time | | | 41.5 32.5 | | ns ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|-------------------|-------------|--------------------------|
| I_{SD} $I_{SDM}^{(1)}$ | Source-drain current Source-drain current (pulsed) | | | | 1.85 7.4 | A A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD}= 1.85\text{ A}$, $V_{GS}=0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD}= 1.85\text{ A}$, $di/dt= 100\text{ A}/\mu\text{s}$, $V_{DD}= 60\text{ V}$ <i>(see Figure 21)</i> | | 476 1.6 6.9 | | ns μC A |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD}= 1.85\text{ A}$, $di/dt= 100\text{ A}/\mu\text{s}$, $V_{DD}= 60\text{ V}$, $T_J=150\text{ }^\circ\text{C}$ <i>(see Figure 21)</i> | | 532 1.9 88 | | ns μC A |

1. Pulse width limited by package
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 9. Gate-source zener diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------------|-------------------------------|---|------|------|------|------|
| $BV_{GSO}^{(1)}$ | Gate-source breakdown voltage | $I_{GS} = \pm 1\text{ mA}$ (open drain) | 30 | | | V |

1. The built in back-to-back zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

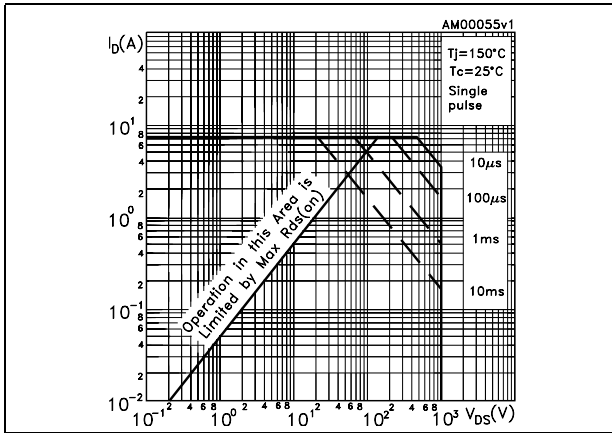


Figure 3. Thermal impedance for TO-220

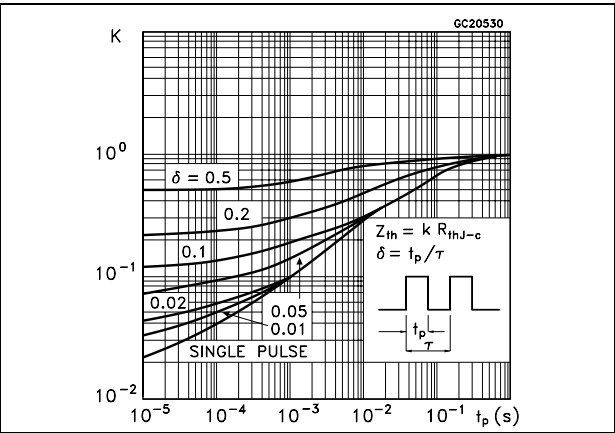


Figure 4. Safe operating area for DPAK, IPAK

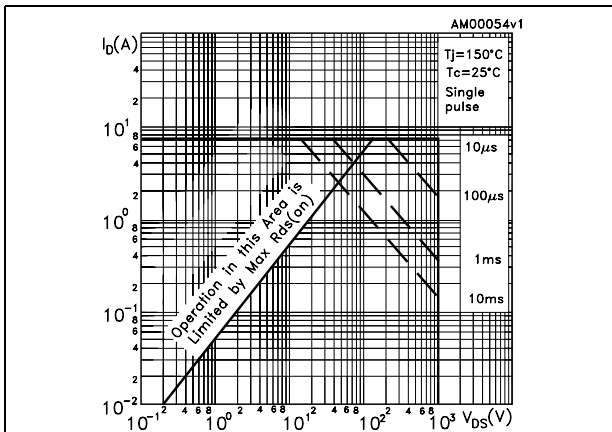


Figure 5. Thermal impedance for DPAK, IPAK

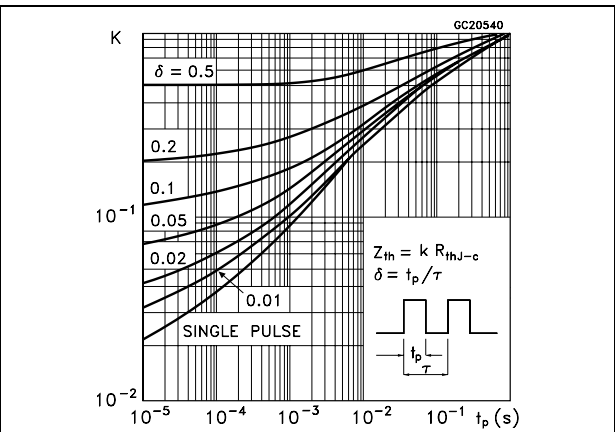


Figure 6. Output characteristics

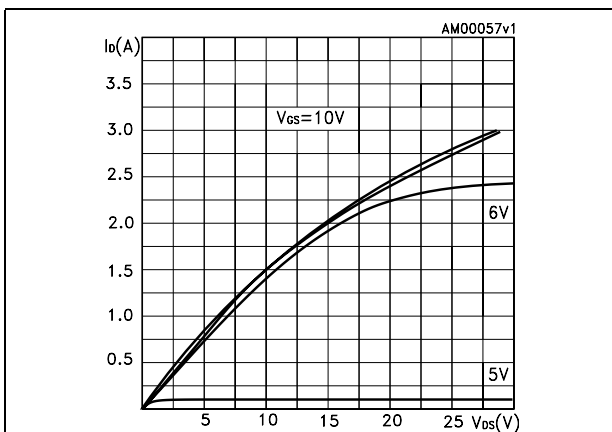


Figure 7. Transfer characteristics

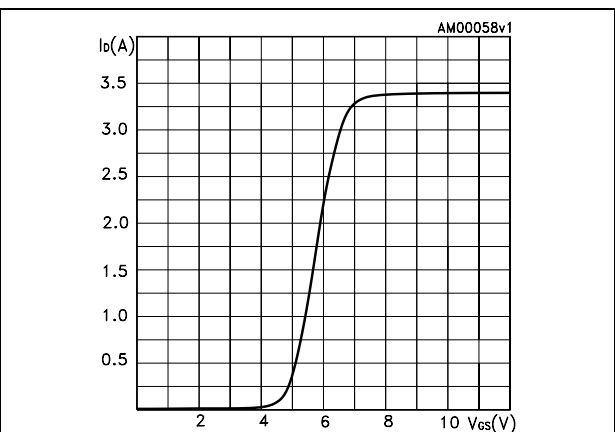


Figure 8. Normalized $B_{V_{DSS}}$ vs temperature

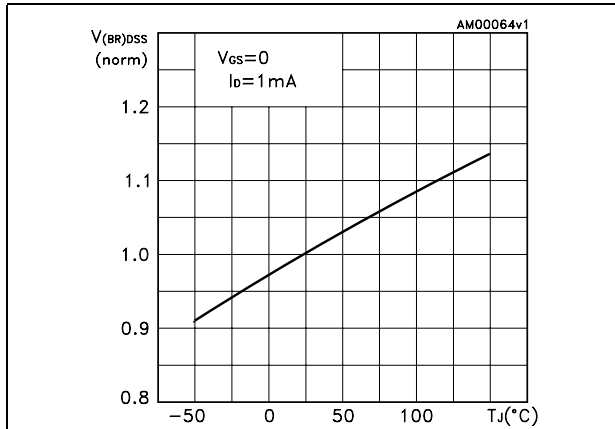


Figure 9. Static drain-source on resistance

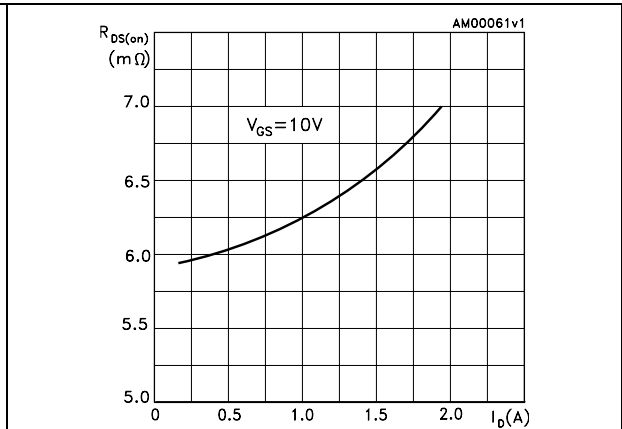


Figure 10. Gate charge vs gate-source voltage

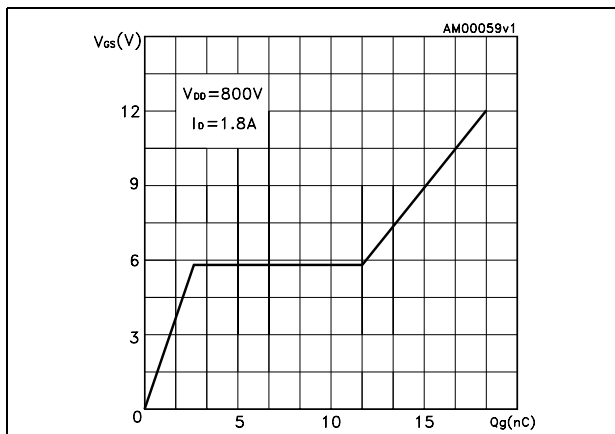


Figure 11. Capacitance variations

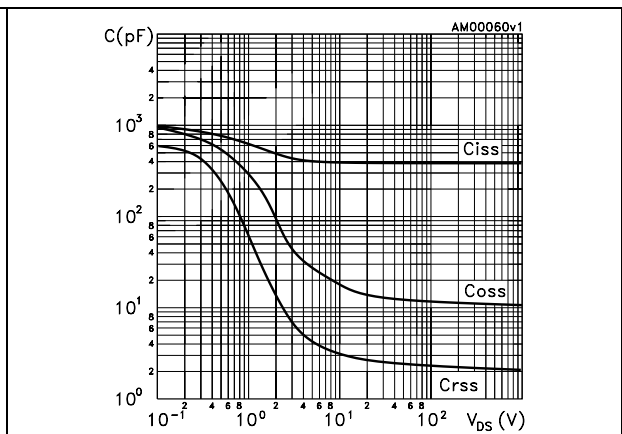


Figure 12. Normalized gate threshold voltage vs temperature

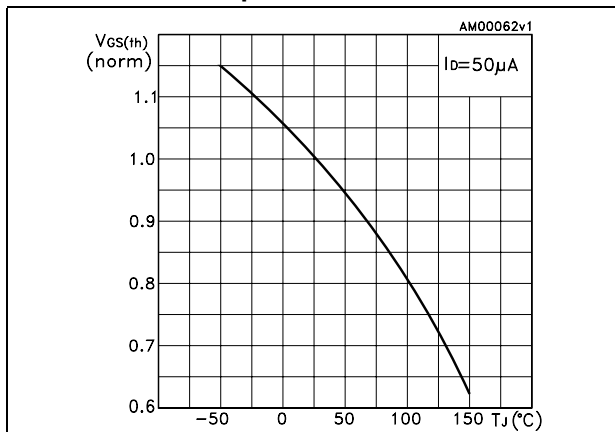


Figure 13. Normalized on resistance vs temperature

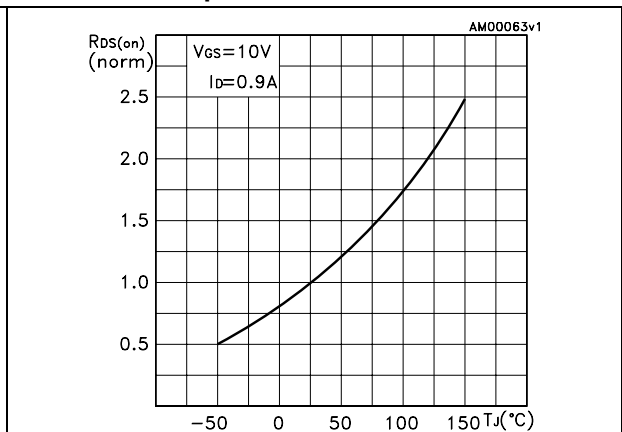


Figure 14. Source-drain diode forward characteristics

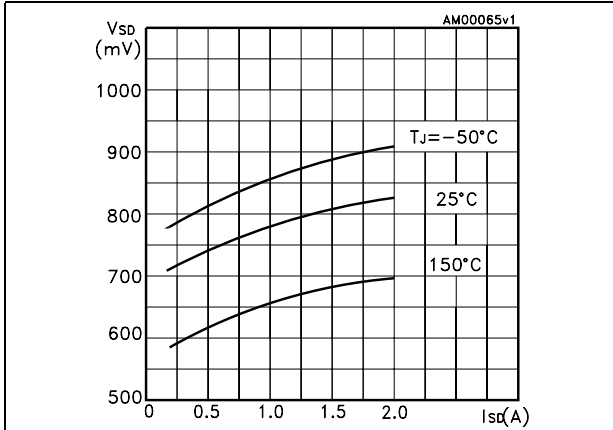
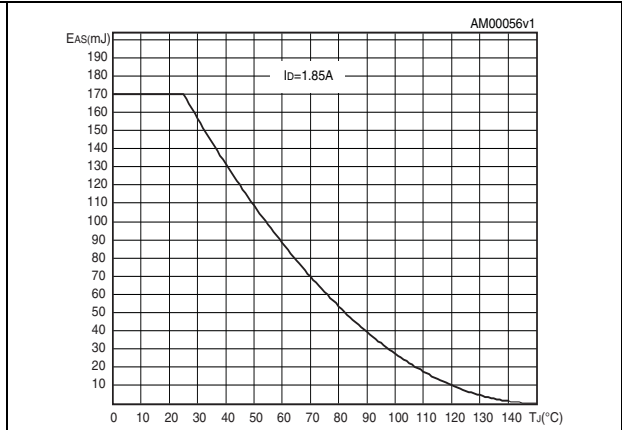


Figure 15. Maximum avalanche energy vs temperature



3 Test circuits

Figure 16. Switching times test circuit for resistive load

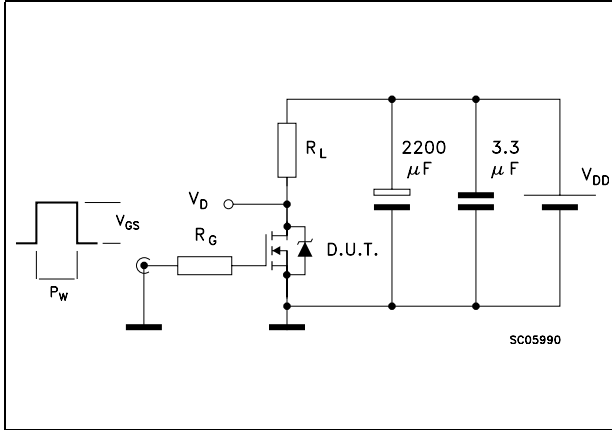


Figure 17. Gate charge test circuit

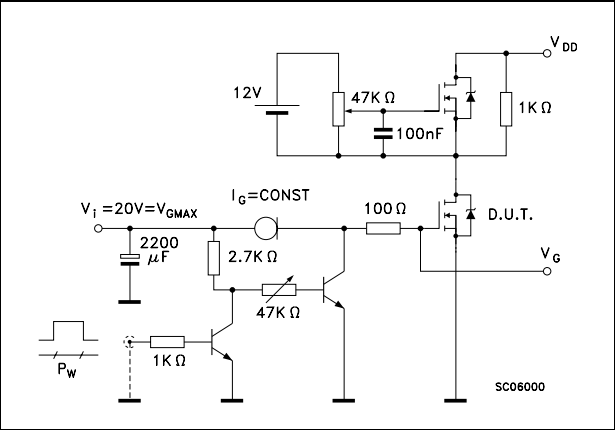


Figure 18. Test circuit for inductive load switching and diode recovery times

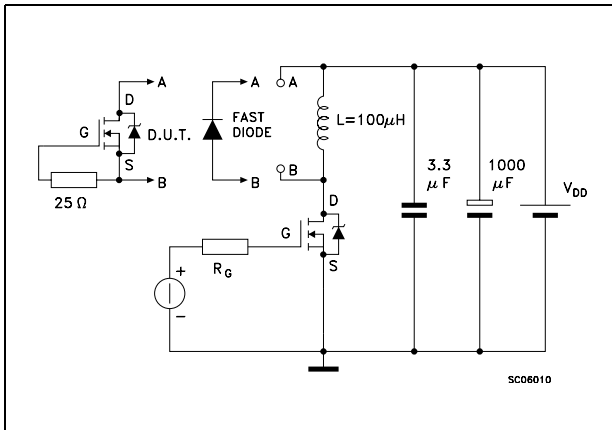


Figure 19. Unclamped inductive load test circuit

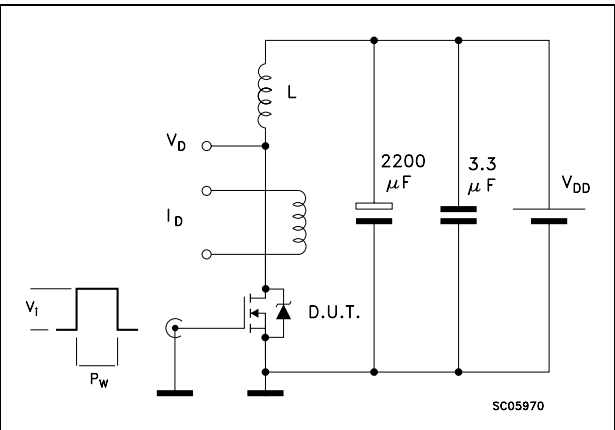


Figure 20. Unclamped inductive waveform

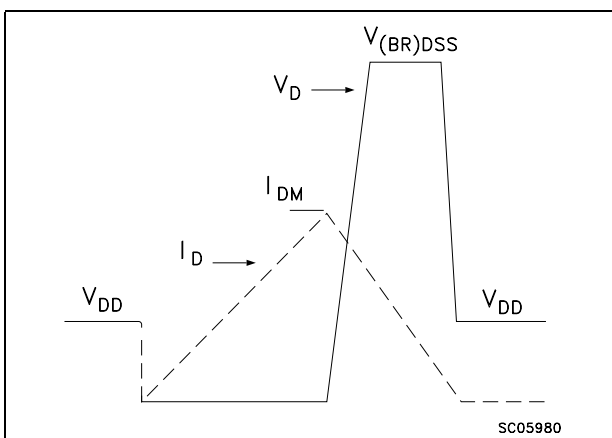
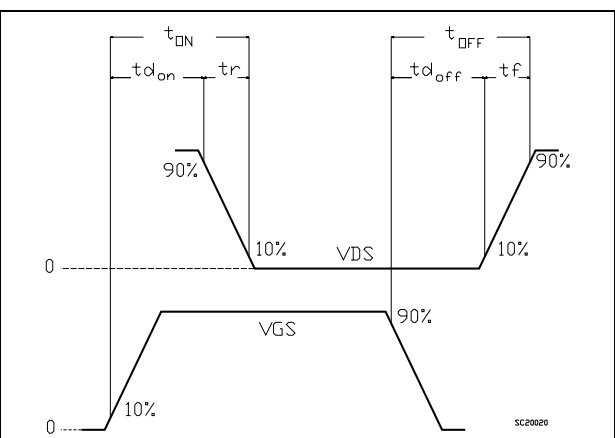


Figure 21. Switching time waveform

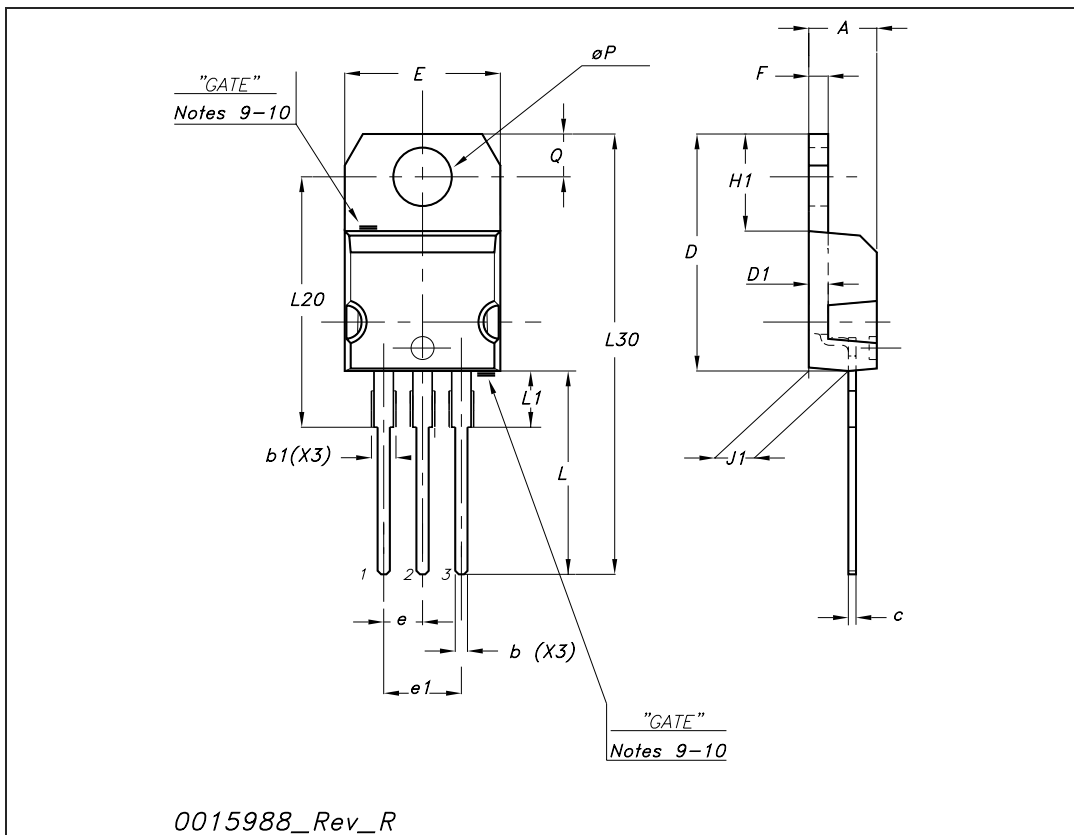


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

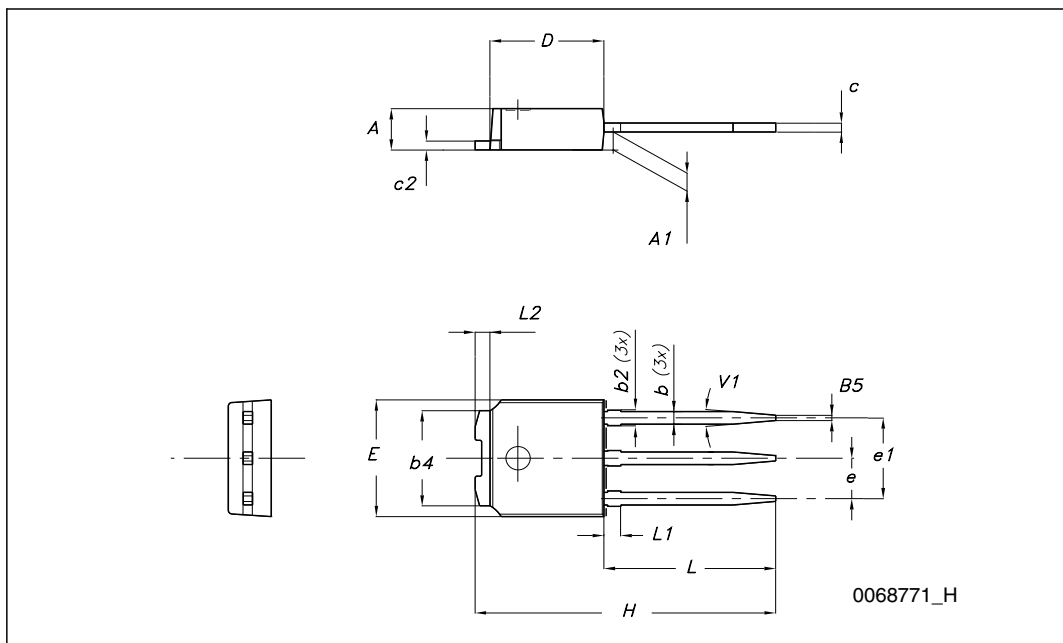
TO-220 mechanical data

| Dim | mm | | | inch | | |
|-----|-------|-------|-------|-------|-------|-------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| c | 0.48 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.6 | | 0.62 |
| D1 | | 1.27 | | | 0.050 | |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.051 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| ∅P | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



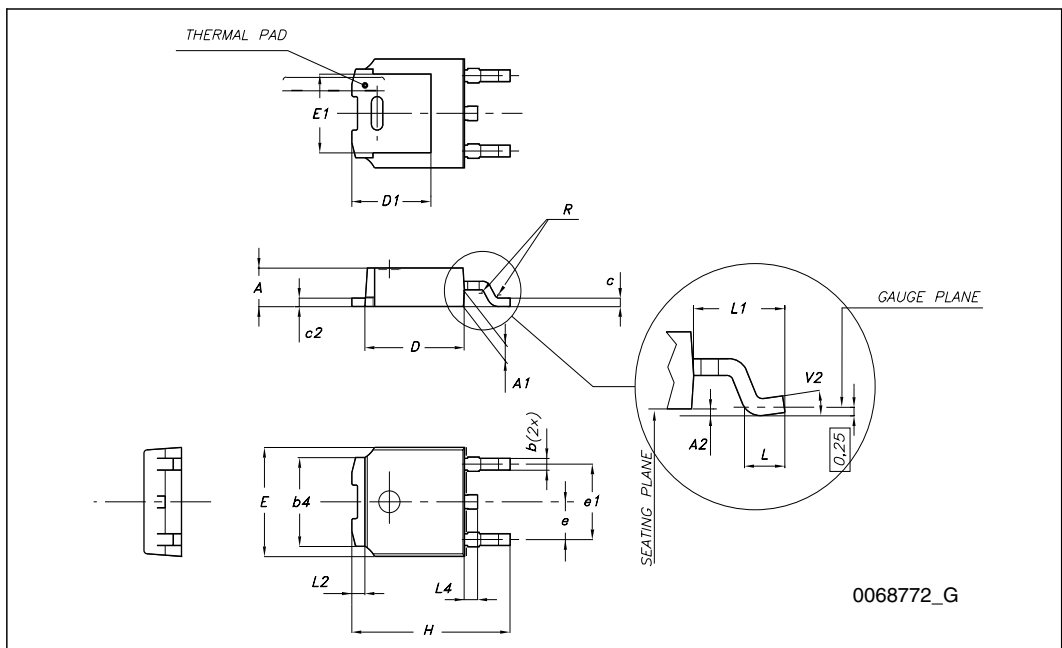
TO-251 (IPAK) mechanical data

| DIM. | mm. | | |
|------|------|-------|------|
| | min. | typ | max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| b | 0.64 | | 0.90 |
| b2 | | | 0.95 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| E | 6.40 | | 6.60 |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | | 16.10 | |
| L | 9.00 | | 9.40 |
| (L1) | 0.80 | | 1.20 |
| L2 | | 0.80 | |
| V1 | | 10° | |



TO-252 (DPAK) mechanical data

| DIM. | mm. | | |
|------|------|------|-------|
| | min. | typ | max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | | 5.10 | |
| E | 6.40 | | 6.60 |
| E1 | | 4.70 | |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1 | | |
| L1 | | 2.80 | |
| L2 | | 0.80 | |
| L4 | 0.60 | | 1 |
| R | | 0.20 | |
| V2 | 0° | | 8° |



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 16.4 | 18.4 | 0.645 | 0.724 |
| N | 50 | | 1.968 | |
| T | | 22.4 | | 0.881 |

| BASE QTY | | BULK QTY | |
|----------|--|----------|--|
| 2500 | | 2500 | |

| DIM. | mm | | inch | |
|------|------|------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 6.8 | 7 | 0.267 | 0.275 |
| B0 | 10.4 | 10.6 | 0.409 | 0.417 |
| B1 | | 12.1 | | 0.476 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.5 | | 0.059 | |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 7.4 | 7.6 | 0.291 | 0.299 |
| K0 | 2.55 | 2.75 | 0.100 | 0.108 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 7.9 | 8.1 | 0.311 | 0.319 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 40 | | 1.574 | |
| W | 15.7 | 16.3 | 0.618 | 0.641 |

6 Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 24-Oct-2007 | 1 | First release |
| 18-Jun-2008 | 2 | – Inserted new package, mechanical data IPAK – Document status promoted from preliminary data to datasheet. |

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